

## IN THE CLAIMS

Please amend the claims as follows:

Claims 1-10 (Canceled)

Claim 11 (New): A process for obtaining a thin layer made of a first material on a substrate made of a second material called a final substrate, the process comprising:

bonding a thick layer of a first material by one of its main faces on the final substrate at an interface;

implanting gaseous species in the thick layer of the first material to create a weakened zone delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material called a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing within the structure composed of the final substrate, the thick layer of the first material and the layer of the third material, at the weakened zone to supply the substrate supporting said thin layer.

Claim 12 (New): The process according to claim 11, wherein implanting gaseous species further comprises implanting one or more identical or different gaseous species.

Claim 13 (New): The process according to claim 12, wherein said gaseous species is selected from the group consisting of a hydrogen and a helium.

Claim 14 (New): The process according to claim 11, wherein the thick layer of the first material is a layer delimited in an initial substrate when implanting a gaseous species to create a weakened zone in the initial substrate, and further comprising fracturing between the

thick layer of the first material and a remainder of the initial substrate, which is performed after bonding the thick layer of the first material onto the final substrate.

Claim 15 (New): The process according to claim 14, wherein implanting gaseous species in the initial substrate further comprises implanting hydrogen ions.

Claim 16 (New): The process according to claim 14, wherein implanting gaseous species in the thick layer of the first material is performed after fracturing between the thick layer of the first material and a remainder of the initial substrate.

Claim 17 (New): The process according to claim 14, wherein implanting gaseous species in the thick layer of first material is performed before bonding the thick layer of the first material on the final substrate.

Claim 18 (New): The process according to claim 17, wherein fracturing is performed by a heat treatment, wherein implanting gaseous species is performed under conditions so that the fracturing between the thick layer of the first material and a remainder of the initial substrate is obtained at a temperature less than the fracture temperature of said structure.

Claim 19 (New): The process according to claim 11, wherein the thick layer of the first material is bonded onto the final substrate by molecular bonding.

Claim 20 (New): The process according to claim 11, wherein a part of the self-supporting layer is deposited, and the gaseous species are implanted in the thick layer of the first material after the partial deposit.